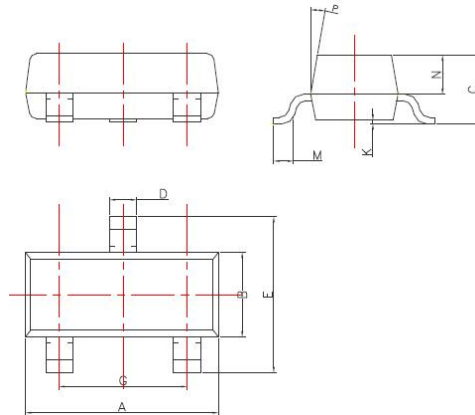
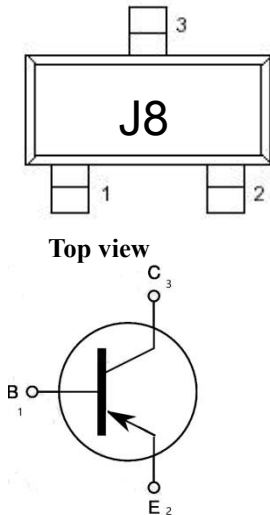


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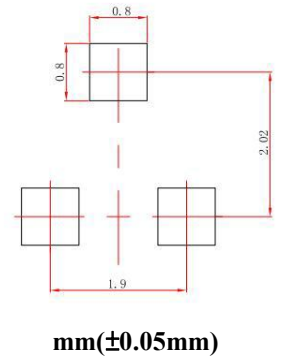
TRANSISTOR

Marking: J8

SOT-23 Dimension

SOT-23
Suggested Layout

DIM	Millimeters
A	2.85~3.04
B	1.30±0.10
C	1.00±0.10
D	0.45±0.05
E	2.25~2.55
G	1.90±0.1
K	0.00~0.10
M	0.20 min
N	0.60±0.10
P	7±2°



MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V _{CEO}	30	Vdc
Collector-Base Voltage	V _{CB0}	19	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current - Continuous	I _C	50	mAdc
Base Current	I _B	50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Collector Power Dissipation	P _c	300	mW
Junction and Storage Temperature	T _j , T _{stg}	150 · -55 ~150	°C

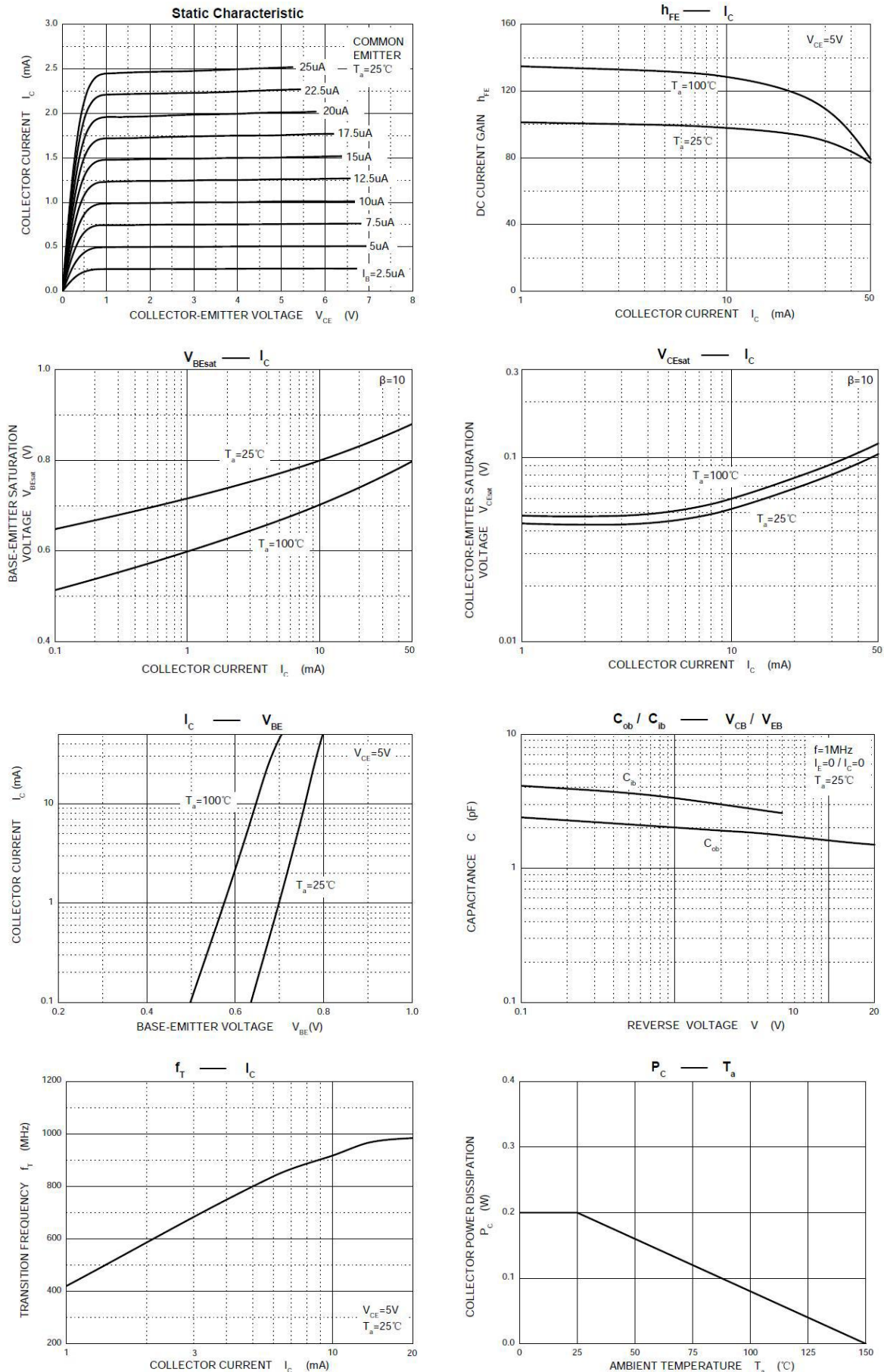
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Type	Max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} =20V, I _E =0	--	--	0.5	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =3V, I _C =0	--	--	0.5	μA
Collector- Base Breakdown Voltage	V _{(BR)CBO}	I _C =100μA	30	--	--	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =1.0mA	19	--	--	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =100μA	4	--	--	V
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =1mA	40	--	300	--
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =10mA, I _B =1mA	--	--	0.6	V
Base Emitter Voltage	V _{BE}	I _B =10mA	--	--	1.0	V
Transition Frequency	f _T	V _{CE} =5V, I _C =10mA	600	1100	--	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz	--	1.2	1.5	pF

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Typical Characteristics



Note: Specifications are subject to change without notice. For more detail and update, please visit our website.